

Marking Information

Site 1



P6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date	Code	Key
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Date Code Key												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		-	-			•	-	~		<u> </u>	N	-

Site 2

P6	ΧWX
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P6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date	Code	Kev
Daic	oouc	T(C)

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	
Code	5		0	1	2	3	4	5	6	7	8	9	
Week		1-	26			27-	-52			5	3		
Code		A	-Z			a-z				2	Z		
Internal Code	Sun		Mon		Tue	W	ed	Thu		Fri		Sat	
Code	Т		U		V	V	V	Х		Y		Z	



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		Vdss	-12	V	
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Drain Current (Note E) \/ 4 E\/	Steady State	T _A = +25°C T _A = +70°C	lD	-3.8 -3.0	А
Continuous Drain Current (Note 5) V_{GS} = -4.5V	t < 5s	T _A = +25°C T _A = +70°C	lо	-5.0 -4.0	А
Maximum Continuous Body Diode Forward Curre	nt (Note 5)		ls	-1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)		ldм	-15	A
Avalanche Current (L = 0.1mH)		IAS	-12	А	
Avalanche Energy (L = 0.1mH)		Eas	8	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	D-	1.4	W	
Total Fower Dissipation (Note 5)	t < 5s	PD	2.2	vv	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	92		
merma Resistance, Junction to Ambient (Note 5)	t < 5s	Reja	55	°C/W	
Thermal Resistance, Junction to Case (Note 5)	Rejc	20			
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C	

Note: 5. Device mounted on 1" \times 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

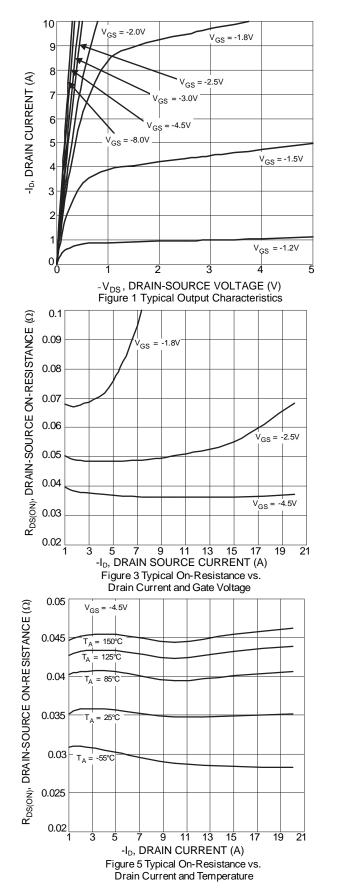
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

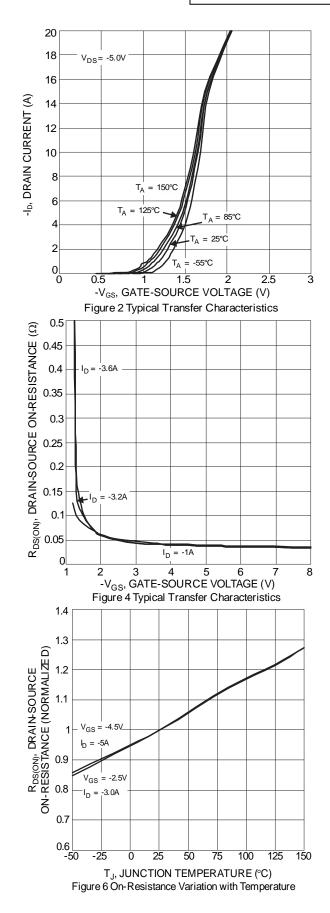
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BVDSS	-12	_	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	—	—	-1.0	μA	$V_{DS} = -12V$, $V_{GS} = 0V$
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	VGS(TH)	-0.4	_	-1	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
		_	37	61		V _{GS} = -4.5V, I _D = -3.6A
Static Drain-Source On-Resistance	R _{DS(ON)}		47	81	mΩ	$V_{GS} = -2.5V, I_D = -3.2A$
		-	63	115		VGS = -1.8V, ID = -1.0A
Diode Forward Voltage	V _{SD}	—	-0.65	-1.2	V	$V_{GS} = 0V, I_{S} = -4.5A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	915	—	pF	
Output Capacitance	Coss		225	—	pF	VDS = -6V, VGS = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss		183	_	pF	1 = 1:00012
Gate Resistance	Rg		56.9	—	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	0		10.7	_	nC	
Total Gate Charge (V _{GS} = -8V)	Qg	—	17.9	—	nC	
Gate-Source Charge	Q _{gs}	—	1.7	—	nC	$V_{DS} = -6V, I_D = -4.3A$
Gate-Drain Charge	Q _{gd}	_	3.0	_	nC	
Turn-On Delay Time	tD(ON)	_	5.7	—	ns	
Turn-On Rise Time	tR	_	11.5	—	ns	$V_{DD} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	tD(OFF)	_	27.8	—	ns	$R_L = 1.6\Omega, R_G = 1\Omega$
Turn-Off Fall Time	tF		26.4	—	ns	7

6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing. Notes:



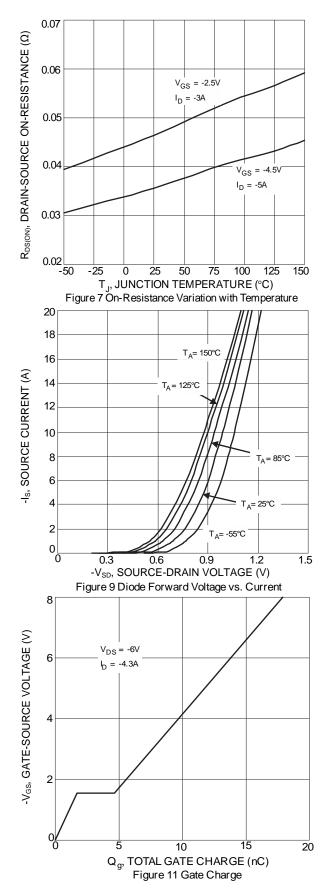
DMP1046UFDB

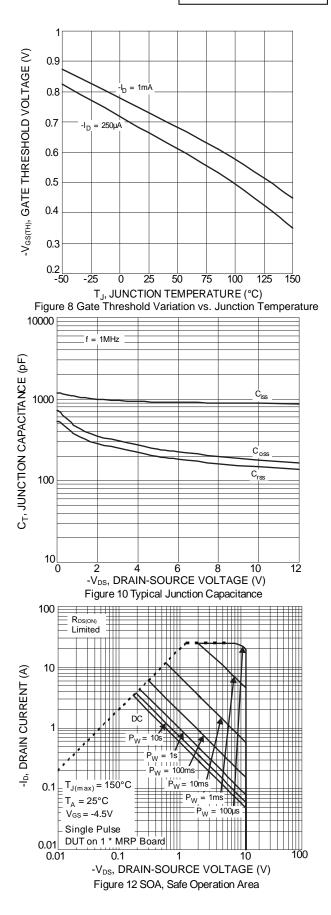




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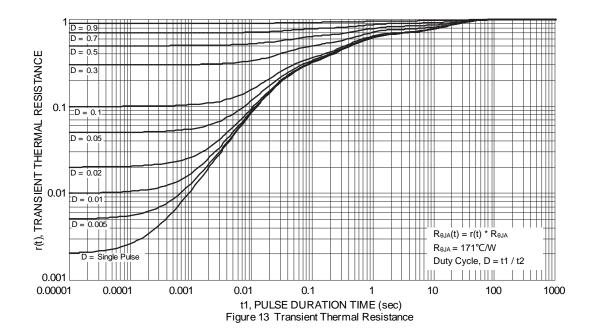




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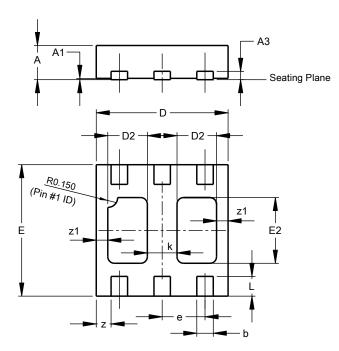






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



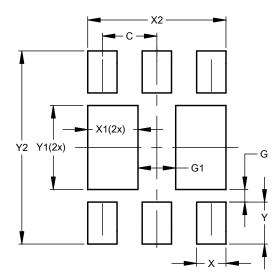
U-DFN2020-6							
	Тур	e B					
Dim	Min	Max	Тур				
Α	0.545	0.605	0.575				
A1	0.00	0.05	0.02				
A3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	0.50	0.70	0.60				
е	-	-	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
k	-	-	0.45				
L	0.25	0.35	0.30				
z	-	-	0.225				
z1	-	-	0.175				
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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